Tim D Veal

List of Publications by Year in Descending Order

162 papers	6,357 citations	46 h-index	73 g-index
170 ext. papers	7,000 ext. citations	4.4 avg, IF	5.47 L-index

#	Paper	IF	Citations
162	Band offsets of metal oxide contacts on TlBr radiation detectors. *Journal of Applied Physics*, **2021**, 130, 175305	2.5	
161	Band alignment of Sb2O3 and Sb2Se3. *Journal of Applied Physics*, **2021**, 129, 235301	2.5	2
160	Indium Gallium Oxide Alloys: Electronic Structure, Optical Gap, Surface Space Charge, and Chemical Trends within Common-Cation Semiconductors. *ACS Applied Materials & Interfaces*, **2021**, 13, 2807-2819	9.5	13
159	Accelerating the development of new solar absorbers by photoemission characterization coupled with density functional theory. *JPhys Energy*, **2021**, 3, 032001	4.9	1
158	Natural Band Alignments and Band Offsets of Sb2Se3 Solar Cells. *ACS Applied Energy Materials*, **2020**, 3, 11617-11626	6.1	7
157	GeSe: Optical Spectroscopy and Theoretical Study of a van der Waals Solar Absorber. *Chemistry of Materials*, **2020**, 32, 3245-3253	9.6	19
156	Vacancy-Ordered Double Perovskite CsTeI Thin Films for Optoelectronics. *Chemistry of Materials*, **2020**, 32, 6676-6684	9.6	26
155	Resonant Ta Doping for Enhanced Mobility in Transparent Conducting SnO. *Chemistry of Materials*, **2020**, 32, 1964-1973	9.6	28
154	Isotype Heterojunction Solar Cells Using n-Type Sb2Se3 Thin Films. *Chemistry of Materials*, **2020**, 32, 2621-2630	9.6	34
153	Sn 5s2 lone pairs and the electronic structure of tin sulphides: A photoreflectance, high-energy photoemission, and theoretical investigation. *Physical Review Materials*, **2020**, 4,	3.2	4
152	How Oxygen Exposure Improves the Back Contact and Performance of Antimony Selenide Solar Cells. *ACS Applied Materials & Interfaces*, **2020**, 12, 52595-52602	9.5	8
151	Influence of Polymorphism on the Electronic Structure of Ga2O3. *Chemistry of Materials*, **2020**, 32, 8460-8470	9.6	21
150	Na2Fe2OS2, a new earth abundant oxysulphide cathode material for Na-ion batteries. *Journal of Materials Chemistry A*, **2020**, 8, 20553-20569	13	5
149	Sb 5s2 lone pairs and band alignment of Sb2Se3: a photoemission and density functional theory study. *Journal of Materials Chemistry C*, **2020**, 8, 12615-12622	7.1	6
148	Resonant doping for high mobility transparent conductors: the case of Mo-doped In2O3. *Materials Horizons*, **2020**, 7, 236-243	14.4	30
147	Identifying Raman modes of Sb2Se3 and their symmetries using angle-resolved polarised Raman spectra. *Journal of Materials Chemistry A*, **2020**, 8, 8337-8344	13	25
146	Nitrogen pair-induced temperature insensitivity of the band gap of GaNSb alloys. *Journal Physics D: Applied Physics*, **2019**, 52, 045105	3	

145	Influence of annealing on the electrical characteristic of GaSbBi Schottky diodes. *Journal of Applied Physics*, **2019**, 126, 053103	2.5	2
144	Chemical etching of Sb2Se3 solar cells: surface chemistry and back contact behaviour. *JPhys Energy*, **2019**, 1, 045001	4.9	7
143	Intrinsic point defects and the n- and p-type dopability of the narrow gap semiconductors GaSb and InSb. *Physical Review B*, **2019**, 100,	3.3	8
142	Band Alignments, Band Gap, Core Levels, and Valence Band States in CuBiS for Photovoltaics. *ACS Applied Materials & Interfaces*, **2019**, 11, 27033-27047	9.5	22
141	Evidence of a second-order Peierls-driven metal-insulator transition in crystalline NbO2. *Physical Review Materials*, **2019**, 3,	3.2	10
140	Transition from electron accumulation to depletion at Ga2O3 surfaces: The role of hydrogen and the charge neutrality level. *APL Materials*, **2019**, 7, 022528	5.7	38
139	Band gap temperature-dependence and exciton-like state in copper antimony sulphide, CuSbS2. *APL Materials*, **2018**, 6, 084904	5.7	12
138	Growth and Characterization of Sb2 Se3 Single Crystals for Fundamental Studies **2018**,		5
137	Band gap temperature-dependence of close-space sublimation grown Sb2Se3 by photo-reflectance. *APL Materials*, **2018**, 6, 084901	5.7	45
136	Self-Compensation in Transparent Conducting F-Doped SnO2. *Advanced Functional Materials*, **2018**, 28, 1701900	15.6	56
135	Atypically small temperature-dependence of the direct band gap in the metastable semiconductor copper nitride Cu3N. *Physical Review B*, **2017**, 95,	3.3	27
134	Optimization of self-catalyzed InAs Nanowires on flexible graphite for photovoltaic infrared photodetectors. *Scientific Reports*, **2017**, 7, 46110	4.9	12
133	Indium-incorporation enhancement of photoluminescence properties of Ga(In)SbBi alloys. *Journal Physics D: Applied Physics*, **2017**, 50, 375102	3	7
132	Valence band modification of Cr2O3 by Ni-doping: creating a high figure of merit p-type TCO. *Journal of Materials Chemistry C*, **2017**, 5, 12610-12618	7.1	24
131	Core Levels, Band Alignments, and Valence-Band States in CuSbS for Solar Cell Applications. *ACS Applied Materials & Interfaces*, **2017**, 9, 41916-41926	9.5	40
130	Hole density and acceptor-type defects in MBE-grown GaSb1-x Bix. *Journal Physics D: Applied Physics*, **2017**, 50, 295102	3	10
129	Electronic and optical properties of single crystal SnS2: an earth-abundant disulfide photocatalyst. *Journal of Materials Chemistry A*, **2016**, 4, 1312-1318	13	190
128	Band gap reduction in InNxSb1-x alloys: Optical absorption, k P modeling, and density functional theory. *Applied Physics Letters*, **2016**, 109, 132104	3.4	9

127	Band Alignments, Valence Bands, and Core Levels in the Tin Sulfides SnS, SnS2, and Sn2S3: Experiment and Theory. *Chemistry of Materials*, **2016**, 28, 3718-3726	9.6	123
126	Direct Measurements of Fermi Level Pinning at the Surface of Intrinsically n-Type InGaAs Nanowires. *Nano Letters*, **2016**, 16, 5135-42	11.5	46
125	Realization of Vertically Aligned, Ultrahigh Aspect Ratio InAsSb Nanowires on Graphite. *Nano Letters*, **2015**, 15, 4348-55	11.5	35
124	Origin of High Mobility in Molybdenum-Doped Indium Oxide. *Chemistry of Materials*, **2015**, 27, 2788-2796	9.6	61
123	Surfactant effect of antimony addition to the morphology of self-catalyzed InAs1− Sb x nanowires. *Nano Research*, **2015**, 8, 1309-1319	10	48
122	Band Gap Dependence on Cation Disorder in ZnSnN2 Solar Absorber. *Advanced Energy Materials*, **2015**, 5, 1501462	21.8	75
121	Increased p-type conductivity in GaNxSb1−, experimental and theoretical aspects. *Journal of Applied Physics*, **2015**, 118, 085708	2.5	6
120	Bi flux-dependent MBE growth of GaSbBi alloys. *Journal of Crystal Growth*, **2015**, 425, 241-244	1.6	24
119	Sb-induced phase control of InAsSb nanowires grown by molecular beam epitaxy. *Nano Letters*, **2015**, 15, 1109-16	11.5	52
118	N incorporation and associated localized vibrational modes in GaSb. *Physical Review B*, **2014**, 89,	3.3	12
117	Ge interface engineering using ultra-thin La2O3 and Y2O3 films: A study into the effect of deposition temperature. *Journal of Applied Physics*, **2014**, 115, 114102	2.5	41
116	Theoretical and experimental studies of electronic band structure for GaSb1−Bix in the dilute Bi regime. *Journal Physics D: Applied Physics*, **2014**, 47, 355107	3	46
115	High Bi content GaSbBi alloys. *Journal of Applied Physics*, **2014**, 116, 043511	2.5	60
114	Graphitic platform for self-catalysed InAs nanowires growth by molecular beam epitaxy. *Nanoscale Research Letters*, **2014**, 9, 321	5	11
113	Bi-induced band gap reduction in epitaxial InSbBi alloys. *Applied Physics Letters*, **2014**, 105, 212101	3.4	38
112	Photoreflectance spectroscopy of GaInSbBi and AlGaSbBi quaternary alloys. *Applied Physics Letters*, **2014**, 105, 112102	3.4	10
111	Valence-band density of states and surface electron accumulation in epitaxial SnO2 films. *Physical Review B*, **2014**, 90,	3.3	50
110	Low- and high-energy photoluminescence from GaSb1−Bixwith 0 . *Applied Physics Express*, **2014**, 7, 111202	2.4	27

109	Contactless electroreflectance and theoretical studies of band gap and spin-orbit splitting in InP1−xBix dilute bismide with x≈0.034. *Applied Physics Letters*, **2014**, 105, 222104	3.4	34
108	Growth of ZnSnN2 by Molecular Beam Epitaxy. *Journal of Electronic Materials*, **2014**, 43, 884-888	1.9	25
107	Growth, disorder, and physical properties of ZnSnN2. *Applied Physics Letters*, **2013**, 103, 042109	3.4	98
106	Growth and properties of GaSbBi alloys. *Applied Physics Letters*, **2013**, 103, 142106	3.4	78
105	Sulfur passivation of surface electrons in highly Mg-doped InN. *Journal of Applied Physics*, **2013**, 114, 103702	2.5	3
104	Temperature dependence of the band gap of GaSb1−xBix alloys with 0 . *Applied Physics Letters*, **2013**, 103, 261907	3.4	40
103	Temperature dependence of the direct bandgap and transport properties of CdO. *Applied Physics Letters*, **2013**, 102, 022102	3.4	55
102	Molecular-beam epitaxy and lattice parameter of GaNxSb1−x: deviation from Vegard's law forx> 0.02. *Journal Physics D: Applied Physics*, **2013**, 46, 264003	3	9
101	Impact of degeneraten-doping on the optical absorption edge in transparent conducting cadmium oxide **2013**,		4
100	The first 25 years of semiconductor muonics at ISIS, modelling the electrical activity of hydrogen in inorganic semiconductors and high-dielectrics. *Physica Scripta*, **2013**, 88, 068503	2.6	17
99	N incorporation in GaInNSb alloys and lattice matching to GaSb. *Journal of Applied Physics*, **2013**, 113, 033502	2.5	18
98	Optical absorption by dilute GaNSb alloys: Influence of N pair states. *Applied Physics Letters*, **2013**, 103, 042110	3.4	20
97	Giant reduction of InN surface electron accumulation: compensation of surface donors by Mg dopants. *Physical Review Letters*, **2012**, 109, 247605	7.4	18
96	Self-compensation in highly n-type InN. *Applied Physics Letters*, **2012**, 101, 011903	3.4	10
95	Epitaxial InGaN on nitridated Si(111) for photovoltaic applications **2012**,		1
94	Structural, electrical and optical characterization of MOCVD grown In-rich InGaN layers. *Journal of Crystal Growth*, **2012**, 358, 51-56	1.6	5
93	Electronic Properties of Post-transition Metal Oxide Semiconductor Surfaces. *Springer Series in Materials Science*, **2012**, 127-145	0.9	4
92	Surface electronic properties of In-rich InGaN alloys grown by MOCVD. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 662-665		4

91	MBE growth and characterization of Mn-doped InN. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2012**, 30, 02B124	1.3	5
90	ZnSnN2: A new earth-abundant element semiconductor for solar cells **2012**,		11
89	Influence of charged-dislocation density variations on carrier mobility in heteroepitaxial semiconductors: The case of SnO2 on sapphire. *Physical Review B*, **2012**, 86,	3.3	12
88	Conductivity in transparent oxide semiconductors. *Journal of Physics Condensed Matter*, **2011**, 23, 334214	1.8	151
87	Polarity effects in the x-ray photoemission of ZnO and other wurtzite semiconductors. *Applied Physics Letters*, **2011**, 98, 101906	3.4	60
86	Controlled nitrogen incorporation in GaNSb alloys. *AIP Advances*, **2011**, 1, 032159	1.5	17
85	Thickness dependence of the strain, band gap and transport properties of epitaxial In2O3 thin films grown on Y-stabilised ZrO2(111). *Journal of Physics Condensed Matter*, **2011**, 23, 334211	1.8	38
84	Stable passivation of InN surface electron accumulation with sulphur treatment. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1605-1607		4
83	Electron mobility in CdO films. *Journal of Applied Physics*, **2011**, 109, 073712	2.5	45
82	Surface, bulk, and interface electronic properties of nonpolar InN. *Applied Physics Letters*, **2010**, 97, 112103	3.4	26
81	Surface band-gap narrowing in quantized electron accumulation layers. *Physical Review Letters*, **2010**, 104, 256803	7.4	80
80	Bulk transport measurements in ZnO: The effect of surface electron layers. *Physical Review B*, **2010**, 81,	3.3	97
79	Observation of shallow-donor muonium in Ga2O3: Evidence for hydrogen-induced conductivity. *Applied Physics Letters*, **2010**, 96, 062110	3.4	61
78	In-vacancies in Si-doped InN. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 1083-1086	1.6	11
77	The influence of Sn doping on the growth of In2O3 on Y-stabilized ZrO2(100) by oxygen plasma assisted molecular beam epitaxy. *Journal of Applied Physics*, **2009**, 106, 013703	2.5	38
76	Unification of the electrical behavior of defects, impurities, and surface states in semiconductors: Virtual gap states in CdO. *Physical Review B*, **2009**, 79,	3.3	69
75	Sulfur passivation of InN surface electron accumulation. *Applied Physics Letters*, **2009**, 95, 192111	3.4	15
74	The donor nature of muonium in undoped, heavily n-type and p-type InAs. *Journal of Physics Condensed Matter*, **2009**, 21, 075803	1.8	1

73	Surface electronic properties of Mg-doped InAlN alloys. *Physica Status Solidi (B): Basic Research*, **2009**, 246, 1169-1172	1.3	2
72	Growth and characterisation of dilute antimonide nitride materials for long-wavelength applications. *Microelectronics Journal*, **2009**, 40, 399-402	1.8	3
71	Valence-band electronic structure of CdO, ZnO, and MgO from x-ray photoemission spectroscopy and quasi-particle-corrected density-functional theory calculations. *Physical Review B*, **2009**, 79,	3.3	106
70	Unintentional conductivity of indium nitride: transport modelling and microscopic origins. *Journal of Physics Condensed Matter*, **2009**, 21, 174201	1.8	35
69	Surface Structure and Electronic Properties of In2O3(111) Single-Crystal Thin Films Grown on Y-Stabilized ZrO2(111). *Chemistry of Materials*, **2009**, 21, 4353-4355	9.6	51
68	Shallow donor state of hydrogen in In2O3 and SnO2: Implications for conductivity in transparent conducting oxides. *Physical Review B*, **2009**, 80,	3.3	116
67	Band gap, electronic structure, and surface electron accumulation of cubic and rhombohedral In2O3. *Physical Review B*, **2009**, 79,	3.3	323
66	Bandgap and effective mass of epitaxial cadmium oxide. *Applied Physics Letters*, **2008**, 92, 022101	3.4	140
65	Band bending at the surfaces of In-rich InGaN alloys. *Journal of Applied Physics*, **2008**, 104, 113716	2.5	32
64	InN/GaN valence band offset: High-resolution x-ray photoemission spectroscopy measurements. *Physical Review B*, **2008**, 78,	3.3	118
63	Valence band offset of the ZnO/AlN heterojunction determined by x-ray photoemission spectroscopy. *Applied Physics Letters*, **2008**, 93, 202108	3.4	69
62	Response to Comment on Bandgap and effective mass determination of epitaxial cadmium oxide[Appl. Phys. Lett. 92, 106103 (2008)]. *Applied Physics Letters*, **2008**, 92, 106104	3.4	1
61	Observation of quantized subband states and evidence for surface electron accumulation in CdO from angle-resolved photoemission spectroscopy. *Physical Review B*, **2008**, 78,	3.3	70
60	Influence of growth conditions and polarity on interface-related electron density in InN. *Journal of Applied Physics*, **2008**, 104, 103703	2.5	15
59	Surface electronic properties of undoped InAlN alloys. *Applied Physics Letters*, **2008**, 92, 172105	3.4	17
58	Surface electronic properties of clean and S-terminated InSb(001) and (111)B. *Journal of Applied Physics*, **2008**, 104, 083709	2.5	17
57	Surface electron accumulation and the charge neutrality level in In2O3. *Physical Review Letters*, **2008**, 101, 116808	7.4	217
56	Determination of the branch-point energy of InN: Chemical trends in common-cation and common-anion semiconductors. *Physical Review B*, **2008**, 77,	3.3	96

55	Valence band density of states of zinc-blende and wurtzite InN from x-ray photoemission spectroscopy and first-principles calculations. *Physical Review B*, **2008**, 77,	3.3	37
54	Nonparabolic coupled Poisson-Schrödinger solutions for quantized electron accumulation layers: Band bending, charge profile, and subbands at InN surfaces. *Physical Review B*, **2008**, 77,	3.3	67
53	Surface electronic properties of n- and p-type InGaN alloys. *Physica Status Solidi (B): Basic Research*, **2008**, 245, 881-883	1.3	16
52	The influence of conduction band plasmons on core-level photoemission spectra of InN. *Surface Science*, **2008**, 602, 871-875	1.8	29
51	Growth and Characterisation of Dilute Antimonide Nitride Materials for Long Wavelength Applications. *Springer Proceedings in Physics*, **2008**, 49-51	0.2	
50	Ab-Initio Studies of Electronic and Spectroscopic Properties of MgO, ZnO and CdO. *Journal of the Korean Physical Society*, **2008**, 53, 2811-2815	0.6	22
49	Variation of band bending at the surface of Mg-doped InGaN: Evidence of p-type conductivity across the composition range. *Physical Review B*, **2007**, 75,	3.3	53
48	In-adlayers on non-polar and polar InN surfaces: Ion scattering and photoemission studies. *Physica B: Condensed Matter*, **2007**, 401-402, 351-354	2.8	12
47	Growth of dilute nitride alloys of GaInSb lattice-matched to GaSb. *Journal of Crystal Growth*, **2007**, 304, 338-341	1.6	8
46	Doping-dependence of subband energies in quantized electron accumulation at InN surfaces. *Physica Status Solidi (A) Applications and Materials Science*, **2007**, 204, 536-542	1.6	4
45	Growth and characterisation of high quality MBE grown InNx Sb1−x. *Physica Status Solidi - Rapid Research Letters*, **2007**, 1, 104-106	2.5	13
44	X-ray photoemission studies of the electronic structure of single-crystalline CdO(100). *Superlattices and Microstructures*, **2007**, 42, 197-200	2.8	17
43	Universality of electron accumulation at wurtzite c- and a-plane and zinc-blende InN surfaces. *Applied Physics Letters*, **2007**, 91, 092101	3.4	96
42	In adlayers on c-plane InN surfaces: A polarity-dependent study by x-ray photoemission spectroscopy. *Physical Review B*, **2007**, 76,	3.3	64
41	Valence band offset of InN/AlN heterojunctions measured by x-ray photoelectron spectroscopy. *Applied Physics Letters*, **2007**, 90, 132105	3.4	81
40	X-ray photoemission spectroscopy determination of the InN/yttria stabilized cubic-zirconia valence band offset. *Applied Physics Letters*, **2007**, 91, 112103	3.4	18
39	Photoluminescence of InNAs alloys: S-shaped temperature dependence and conduction-band nonparabolicity. *Physical Review B*, **2007**, 76,	3.3	29
38	Dilute antimonide nitrides for very long wavelength infrared applications **2006**, 6206, 201		13

37	Origin of the n-type conductivity of InN: The role of positively charged dislocations. *Applied Physics Letters*, **2006**, 88, 252109	3.4	134
36	Band anticrossing in GaNxSb1-x. *Applied Physics Letters*, **2006**, 89, 111921	3.4	49
35	Quantized electron accumulation states in indium nitride studied by angle-resolved photoemission spectroscopy. *Physical Review Letters*, **2006**, 97, 237601	7.4	91
34	Transition from electron accumulation to depletion at InGaN surfaces. *Applied Physics Letters*, **2006**, 89, 202110	3.4	76
33	Electron depletion at InAs free surfaces: Doping-induced acceptorlike gap states. *Physical Review B*, **2006**, 73,	3.3	59
32	Dielectric function of degenerate InSb: Beyond the hydrodynamic model. *Physical Review B*, **2006**, 73,	3.3	3
31	InN: Fermi level stabilization by low-energy ion bombardment. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1841-1845		4
30	Scanning tunnelling spectroscopy of quantized electron accumulation at InxGa1-xN surfaces. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 85-92	1.6	16
29	Inversion and accumulation layers at InN surfaces. *Journal of Crystal Growth*, **2006**, 288, 268-272	1.6	33
28	Growth of dilute GaNSb by plasma-assisted MBE. *Journal of Crystal Growth*, **2005**, 278, 188-192	1.6	28
27	Photoelectron spectroscopy study of Ga1-xMnxAs(0 0 1) surface oxide and low temperature cleaning. *Surface Science*, **2005**, 585, 66-74	1.8	10
26	InN{0001} polarity by ion scattering spectroscopy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2301-2304		4
25	Electron accumulation at InN/AlN and InN/GaN interfaces. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2246-2249		18
24	Photoluminescence spectroscopy of bandgap reduction in dilute InNAs alloys. *Applied Physics Letters*, **2005**, 87, 182114	3.4	47
23	Valence-band structure of InN from x-ray photoemission spectroscopy. *Physical Review B*, **2005**, 72,	3.3	55
22	Clean wurtzite InN surfaces prepared with atomic hydrogen. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2005**, 23, 617-620	2.9	47
21	Band gap reduction in GaNSb alloys due to the anion mismatch. *Applied Physics Letters*, **2005**, 87, 132101	3.4	44
20	Electron spectroscopy of dilute nitrides. *Journal of Physics Condensed Matter*, **2004**, 16, S3201-S3214	1.8	7

19	Fuchs□Kliewer phonon excitations in GaNAs alloys. *Journal of Applied Physics*, **2004**, 95, 8466-8468	2.5	1
18	Indium nitride: Evidence of electron accumulation. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 2175		37
17	Negative band gaps in dilute InNxSb1-x alloys. *Physical Review Letters*, **2004**, 92, 136801	7.4	47
16	Temperature invariance of InN electron accumulation. *Physical Review B*, **2004**, 70,	3.3	38
15	Core-level photoemission spectroscopy of nitrogen bonding in GaNxAs1□ alloys. *Applied Physics Letters*, **2004**, 85, 1550-1552	3.4	27
14	Low-energy nitrogen ion implantation of InSb. *Journal of Applied Physics*, **2004**, 96, 4935-4938	2.5	10
13	Intrinsic electron accumulation at clean InN surfaces. *Physical Review Letters*, **2004**, 92, 036804	7.4	426
12	Origin of electron accumulation at wurtzite InN surfaces. *Physical Review B*, **2004**, 69,	3.3	189
11	Sulphur-induced electron accumulation on InAs: a comparison of the (001) and (111)B surfaces. *Surface Science*, **2003**, 544, 320-328	1.8	21
10	Determination of the substitutional nitrogen content and the electron effective mass in InNxSb1□ (001) epitaxial layers. *IEE Proceedings: Optoelectronics*, **2003**, 150, 102		2
9	Passivation and reconstruction-dependent electron accumulation at sulphur treated InAs() surfaces. *Surface Science*, **2003**, 523, 179-188	1.8	25
8	Effect of hydrogen in dilute InNxSb1□ alloys grown by molecular beam epitaxy. *Applied Physics Letters*, **2003**, 83, 1776-1778	3.4	17
7	Electron dynamics in InNxSb1□. *Applied Physics Letters*, **2003**, 83, 2169-2171	3.4	7
6	Extreme band bending at MBE-grown InAs(001) surfaces induced by in situ sulphur passivation. *Journal of Crystal Growth*, **2002**, 237-239, 196-200	1.6	9
5	Plasmon damping in molecular beam epitaxial-grown InAs(100). *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 1766		2
4	HREELS and photoemission study of GaSb()-(1□) surfaces prepared by optimal atomic hydrogen cleaning. *Surface Science*, **2002**, 499, 251-260	1.8	19
3	Profiling of electron accumulation layers in the near-surface region of InAs (110). *Physical Review B*, **2001**, 64,	3.3	25
2	Temperature-dependent two-dimensional plasmons at clean and hydrogenated Ge(001) surfaces. *Physical Review B*, **2000**, 62, 7330-7335	3.3	3

1	Controlled oxide removal for the preparation of damage-free InAs(110) surfaces. *Applied Physics Letters*, **2000**, 77, 1665-1667	3.4	17